

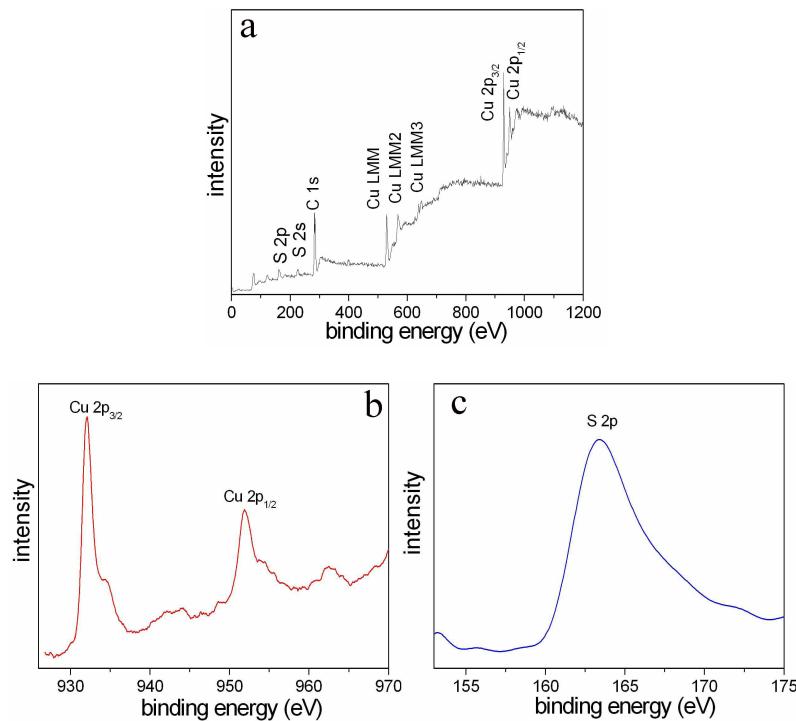
**Supplementary Material For**  
**Dynamic isomers engaged fabrication of copper sulfide rattle-type structures and**  
**their optoelectronic properties**

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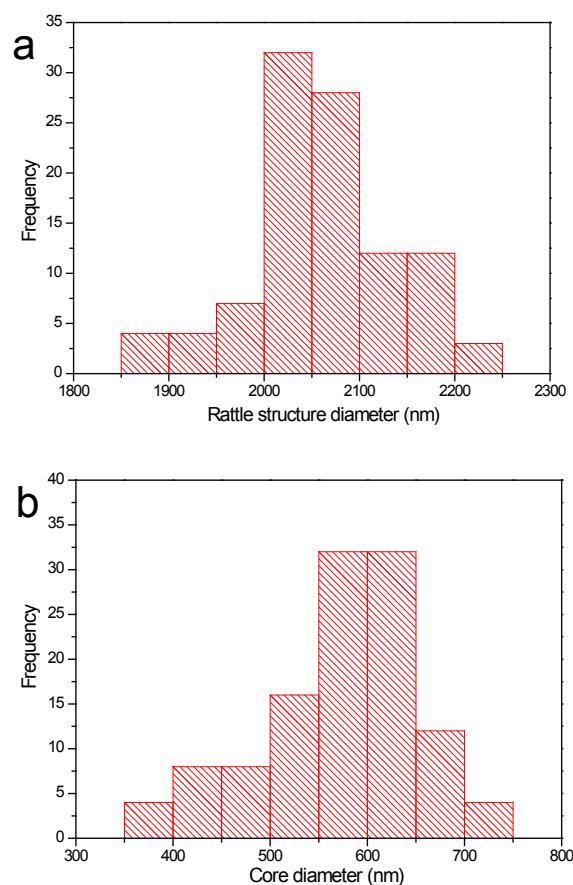
### 1. XPS results

The XPS survey spectrum in **Fig. S1** reveals that the obtained sample consists of Cu and S. The binding energies of all spectra were corrected by referencing the C1s value of 284.6 eV. The high-resolution XPS spectra of Cu 2p and S 2p region are shown in figure 1b and 1c. The spectrum of the Cu 2p signal reveals that the binding energy of Cu 2p<sub>3/2</sub> and Cu 2p<sub>1/2</sub> is 932.5 eV and 952.2 eV. The sulfur 2p peaks are located at 162.7 eV, which are consistent with the 160-164 eV range expected for S in sulfide phase.<sup>1</sup>



**Fig. S1** (a) XPS survey spectrum; (b) and (c) high-resolution XPS spectra of Cu 2p and S 2s.

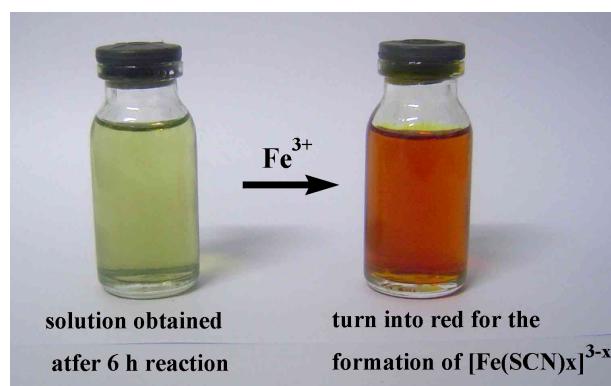
## 2. Size distribution



**Fig. S2** Size distribution of (a) the rattle type structure and (b) the core.

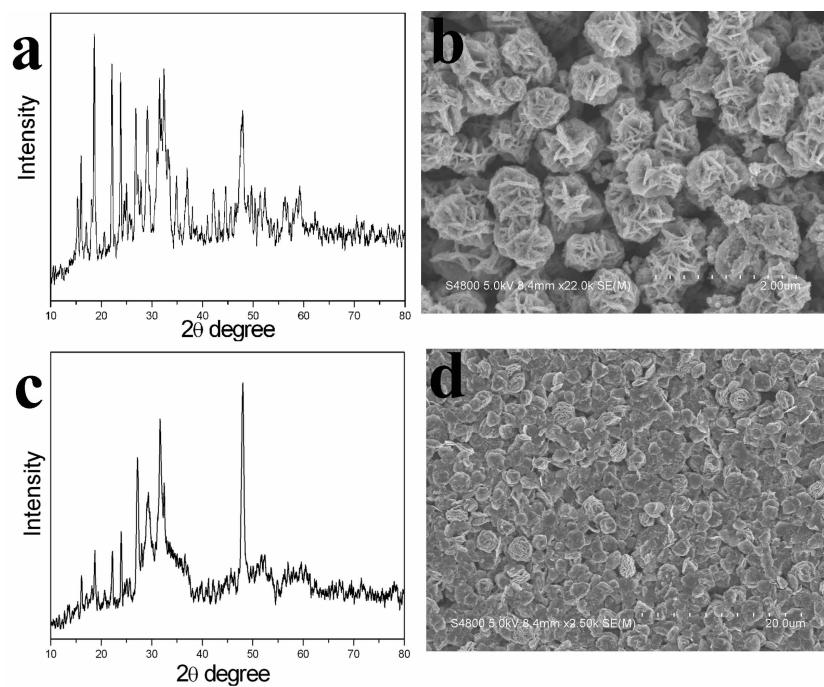
## 3. The reaction between the centrifugated solution and $\text{Fe}^{3+}$

The centrifugated solution obtained at 6 hours turn into red for the formation of  $[\text{Fe}(\text{SCN})_x]^{3-x}$ . When  $\text{Fe}^{3+}$  was added into it



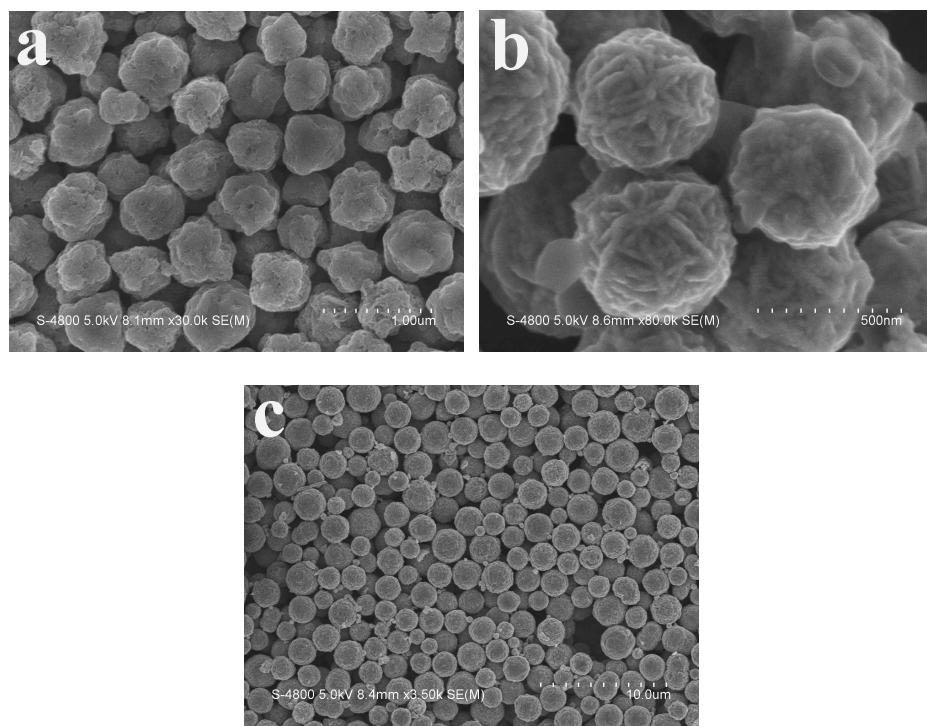
**Fig. S3** Digital photo of the solution before and after  $\text{Fe}^{3+}$  added.

## 4. The effect of anions



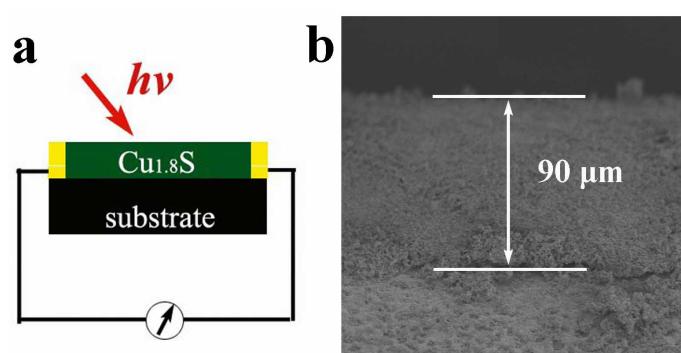
**Fig. S4** XRD pattern and SEM image of intermediate obtained at 4 h with (a and b) CuSO<sub>4</sub>, (c and d) CuCl<sub>2</sub>·2H<sub>2</sub>O.

## 5. SEM evolution process



**Fig. S5** SEM image of the evolution process of Cu<sub>1.8</sub>S RTS after (a) 1 h, (b) 6 h and (c) 1 day reaction.

## 6. Optoelectronic device



**Fig. S6** (a) sketch map of setting for photocurrent measurement; (b) SEM image of the prepared Cu<sub>1.8</sub>S film.

## References

1. Y. F. Liu, J. B. Cao, Y. Y. Wang, J. H. Zeng and Y. T. Qian. *Inorg. Chem. Commun.* 2002, **5**, 407–410.